20. A material according to claim 18, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher at a stage where a semiconductor has been bonded to a support member with said material.

21. A material according to claim 20, said material having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

22. A material according to claim 17, said material having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

23. A material according to claim 22, having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher at a stage where a semiconductor has been bonded to a support member with said material.

24. A material comprising an organic die-bonding film having a saturation moisture absorption of 1.0% by volume or less.

25 A material comprising an organic die-bonding film having a residual volatile component in an amount of not more than 3.0% by weight.

26. A material according to claim 24, having a residual volatile component in an amount of not more than 3.0% by weight.

27. A material comprising an organic die-bonding film having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

28. A material comprising an organic die-bonding film having a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor has been bonded to said support member.

29. A material comprising an organic die-bonding film having a peel strength of 0.5 kgf/5 mm x 5 mm chip or higher at a stage where a semiconductor has been bonded to a support member with said material.

30. A material according to claim 29, having a saturation moisture absorption of 1.0% by volume or less.

31. A material according to claim 29, having a residual volatile component in an amount of not more than 3.0% by weight.

32. A material according to claim 30, having a residual volatile component in an amount of not more than 3.0% by weight.

33. A material according to claim 29, having a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

34. A material according to claim 17, including at least one component selected from an epoxy resin, a silicon resin, an acryl resin and a polyimide resin.

35. A material according to claim 34, said component including a polyimide resin.

36. A material according to claim 34, said component including an epoxy resin, said epoxy resin being any one of glycidyl ether, glycidylamine, glycidyl ester and an alicyclic epoxy resin.

37. A material according to claim 27, including at least one component selected from an epoxy resin, a silicon resin, an acryl resin and a polyimide resin.

38. A material according to claim 37, said component including a polyimide resin.

39. A material comprising an organic die-bonding film according to claim 21, said component including an epoxy resin, said epoxy resin being any one of glycidyl ether, glycidylamine, glycidyl ester and an alicyclic epoxy resin.

40. A material comprising an organic die-bonding film according to claim 1, further including an inorganic filler.

41. A material comprising an organic die-bonding film according to claim 27, further including an inorganic filler.

42. A method of bonding a semiconductor chip to a support member wherein said material comprising an organic die-bonding film according to claim 17 is used for said bonding.

43. A method of bonding according to claim 42, wherein said bonding is carried out at a temperature of 100-350°C for a time period of 0.1 second - 20 seconds with a pressure of 0.1 - 20gf/mm^2.

44. A method of bonding according to claim 43, wherein said bonding is carried out at a temperature of 150 - 250°C for a time period not longer than 2 seconds, with a pressure of 4 gf/mm^2 or less.

45. A method of bonding according to claim 44, wherein said bonding is carried out for a time period 1.5 seconds or less, with a pressure of 0.3 - 2 gf/mm^2.

46. A method of bonding the support member to the semiconductor chip with a material comprising an organic die-bonding film according to claim 27.

47. A method of bonding according to claim 46, wherein said bonding is carried out at a temperature of 100 - 350°C for a time period of 0.1 second - 20 seconds with a pressure of 0.1-20 gf/mm^2.

48. A method of bonding according to claim 47, wherein said bonding is carried out at a temperature of 150 - 250°C for a time period of less than 2 seconds with a pressure of 4 gf/mm^2.

49. A method of bonding according to claim 48, wherein said bonding is carried out for a time period of 1.5 seconds or less with a pressure of 0.3-2 gf/mm^2.

50. A semiconductor device manufactured using a material comprising an organic die-bonding film according to claim 17.

51. A semiconductor device manufactured using a material comprising an organic die-bonding film according to claim 27.